Multivariate Synthesis of Tin Phosphide

Nanoparticles: Temperature, Time, and Ligand

Control of Size, Shape, and Crystal Structure

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Supporting Information

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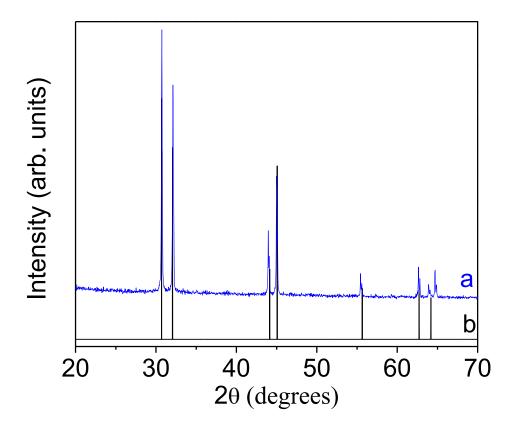


Figure S1. (a) Powder XRD pattern of the product obtained from the reaction of SnCl₂ and TOP in OLA/OA/ODE at 350 °C for 3 h along with the (b) ICDD-PDF overlay of tetragonal Sn (JCPDS No. 00-004-0673).

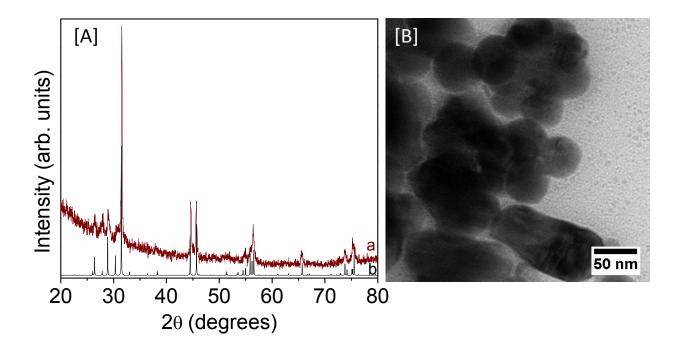


Figure S2. (A) (a) Powder XRD pattern of the product obtained from the reaction of SnCl₂ and (TMSi)₃P in OLA/OA/ODE at 180 °C for 3 min along with the (b) ICDD-PDF overlay of rhombohedral Sn₄P₃ (JCPDS No. 01-073-1820). (B) A representative TEM image of the asprepared particles.

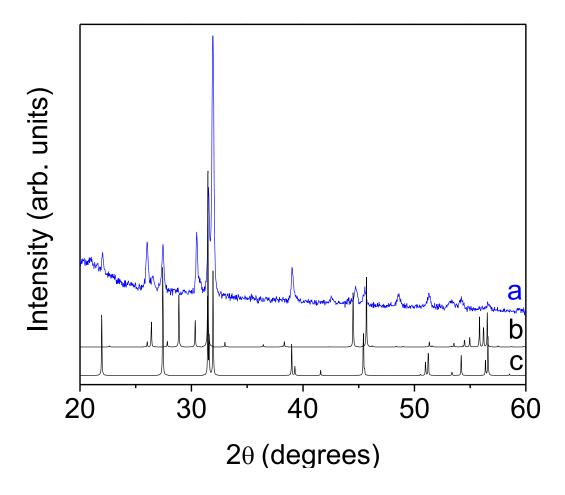


Figure S3. (a) Powder XRD pattern of the product obtained from the reaction of SnCl₂ and (TMSi)₃P in OLA/OA/ODE with DDT at 180 °C for 12 h along with the ICDD- PDF overlays of (b) rhombohedral Sn₄P₃ (JCPDS No. 01-073-1820) and (c) orthorhombic SnS (JCPDS No. 39-0354).

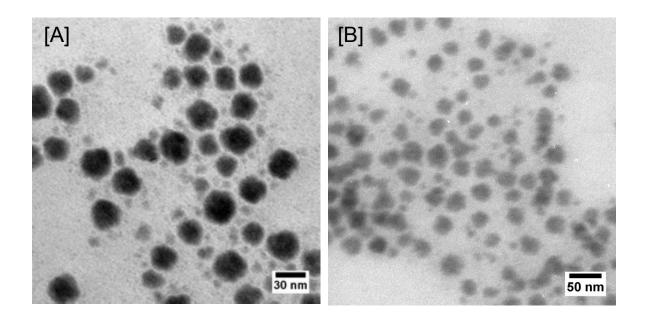


Figure S4. Representative TEM images of (A) rhombohedral Sn₄P₃ NPs synthesized at 180 °C and (B) hexagonal SnP NCs synthesized at 250 °C with no use of oleic acid.

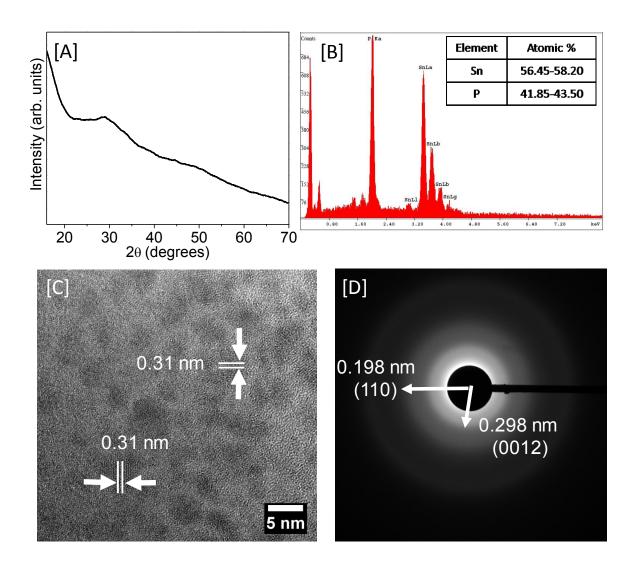


Figure S5. (A) A representative powder XRD pattern of amorphous to partially crystalline Sn₄P₃ NPs produced at 180 °C for 5 min using SnI₄ and (TMSi)₃P precursors, without the use of alkylphosphines (TBP or TOP). (B) SEM/EDS spectrum of the corresponding Sn₄P₃ NPs along with (C) HRTEM, and (D) the selected area electron diffraction pattern recorded from 200 nm x 200 nm area of the sample indicating short-range crystalline order of rhombohedral Sn₄P₃. The broad and not well defined peaks in the PXRD is due to lack of long-range crystalline order. The average Sn: P atomic ratio obtained from 5 individual measurements of the same sample are also shown suggesting the growth of Sn₄P₃ particles.

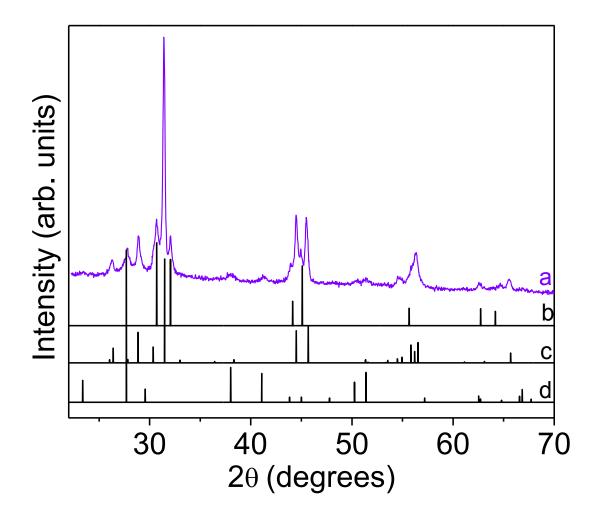


Figure S6. (a) Powder XRD pattern of the product obtained from the reaction of SnI₄ and (TMSi)₃P in OLA/OA/ODE at 180 °C for 3 min in the presence of 12 mM TBP. ICDD-PDF overlays of (b) tetragonal tin (JCPDS No. 00-004-0673), (c) rhombohedral Sn₄P₃ (JCPDS No. 01-073-1820), and (d) hexagonal SnP (JCPDS No. 03-065-9787) are also shown.

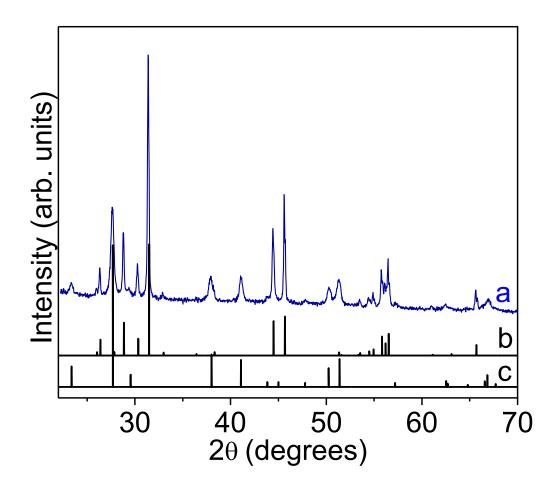


Figure S7. (a) Powder XRD pattern of the product obtained from the reaction of SnI₄ and (TMSi)₃P in OLA/OA/ODE at 180 °C for 3 min in the presence of 4 mM of TOP. ICDD-PDF overlays of (b) rhombohedral Sn₄P₃ (JCPDS No. 01-073-1820) and (c) hexagonal SnP (JCPDS No. 03-065-9787) are also shown.

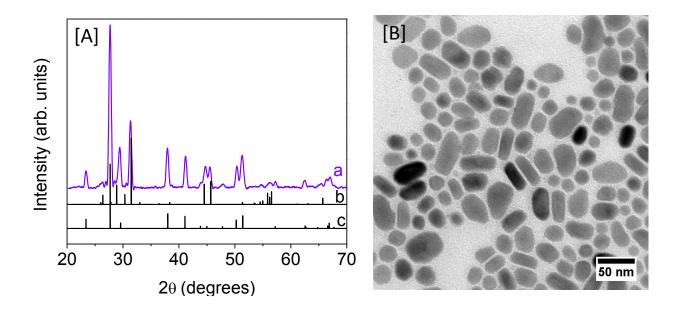


Figure S8. (A) Powder XRD pattern of (a) the product obtianed from the reaction of SnI₄ and (TMSi)₃P in OLA/OA/ODE at 220 °C for 15 min. ICDD-PDF overlays of (b) rhombohedral Sn₄P₃ (JCPDS No. 01-073-1820) and (c) hexagonal SnP (JCPDS No. 03-065-9787) are also shown. (B) A representative TEM image of the as-prepared particles.

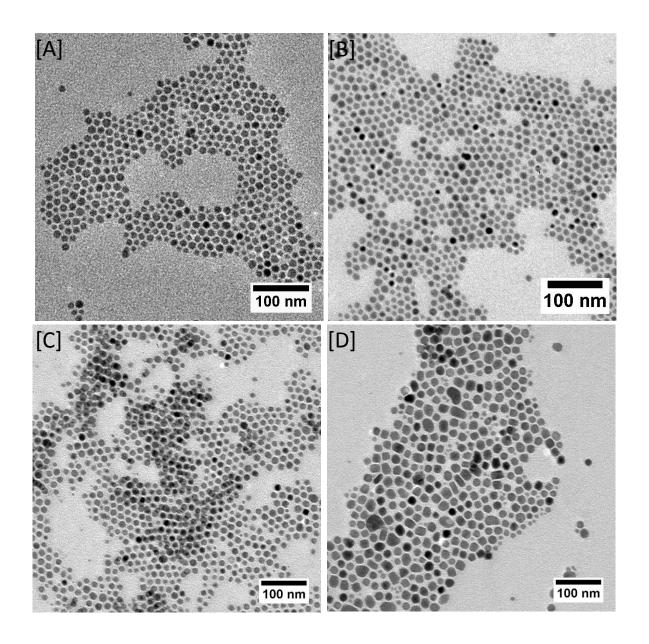


Figure S9. Representative TEM images of the phase pure hexagonal SnP NCs synthesized in OLA/OA/ODE at 250 °C for (a) 5, (b) 30, (c) 60, and (c) 180 seconds.

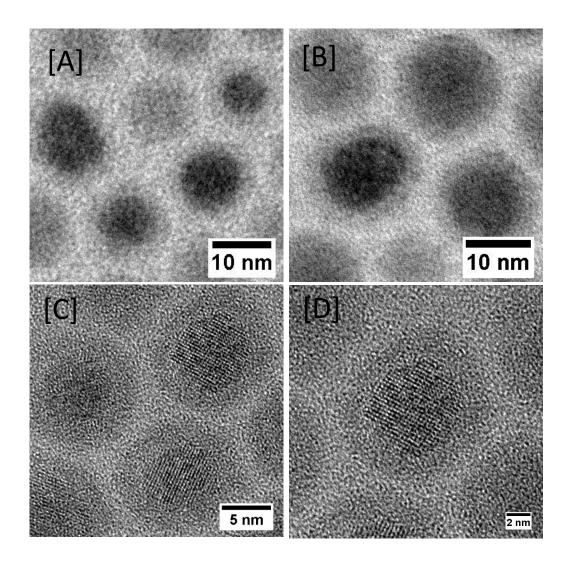


Figure S10. Low resolution and high resolution TEM images of the hexagonal SnP NCs prepared in OLA/OA/ODE at 250 °C for (a) 5, (b) 30, (c) 60, and (c) 180 seconds showing the presence of a crystalline SnP core and amorphous shell with varying thickness.

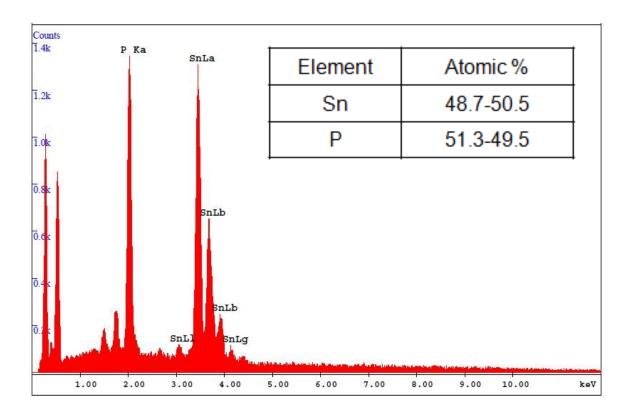


Figure S11. A representative SEM/EDS spectrum of the hexagonal SnP NCs synthesized at 250 °C without the use of TBP for 60 seconds. The average Sn: P atomic ratio obtained from 5 individual measurements of the same sample are also shown.

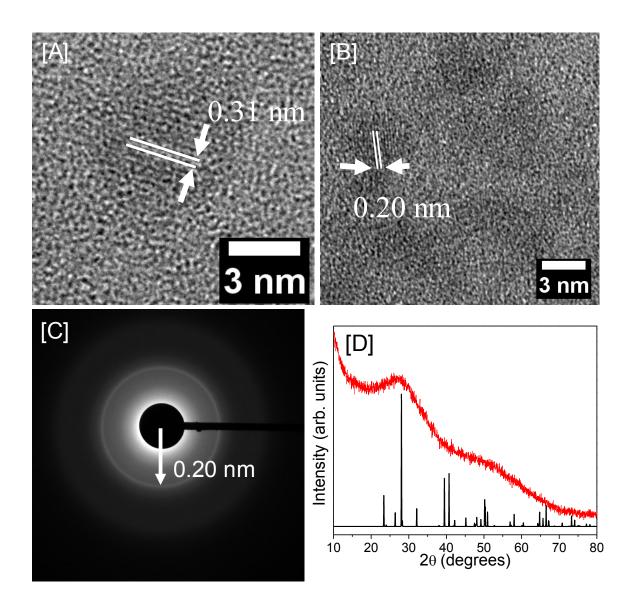


Figure S12. (A-B) HRTEM images of trigonal Sn₃P₄ NPs synthesized at 100 °C for 3 min using SnI₄ and (TMSi)₃P in OLA/OA/ODE in the presence of TBP. (C) SAED and (D) PXRD patterns of the corresponding sample along with ICDD-PDF overlay of trigonal Sn₃P₄ generated from crystal maker (black lines).¹

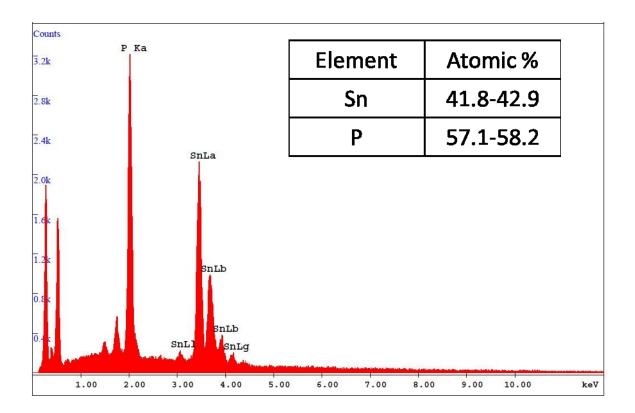


Figure S13. Representative SEM/EDS spectrum of trigonal Sn_3P_4 NPs synthesized in OLA/OA/ODE at 100 °C with 4 mM TBP for 60 sec. The average Sn: P atomic ratio obtained from 5 individual measurements of the same sample are also shown.

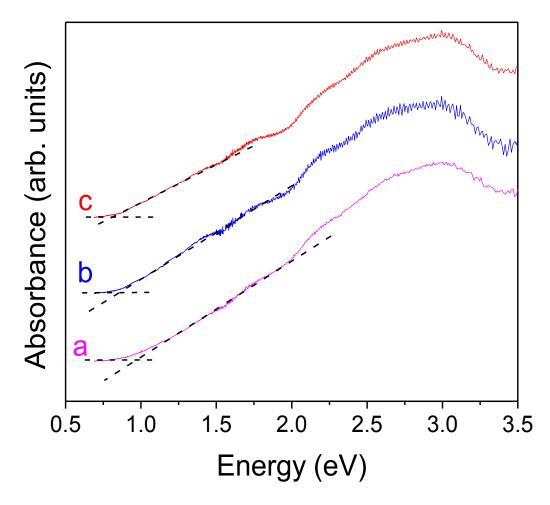


Figure S14. Diffuse reflectance spectra (converted to absorption using Kubelka-Munk remission function) of trigonal Sn₃P₄ NPs synthesized in OLA/OA/ODE without TBP at 100 °C for (a) 1, (b) 2, and (c) 3 minutes.

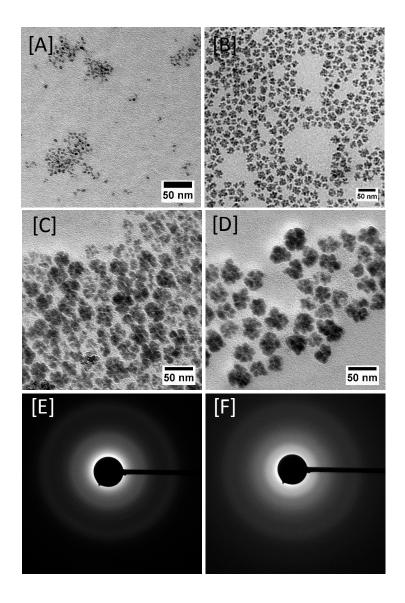


Figure S15. Representiavtive TEM images of trigonal Sn₃P₄ NPs synthesized in OLA/OA/ODE at 100 °C without TBP for (A) 5 sec, (B) 1 min, (C) 2 min, and (D) 3 min. (E) and (F) are electron diffraction patterns of NPs shown in (C) and (D), respectively.

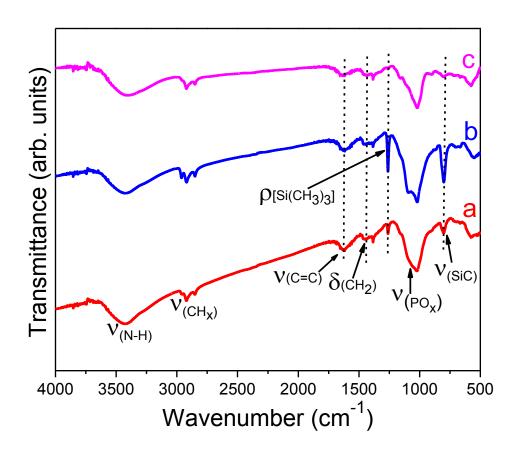


Figure S16. FT-IR spectra of tin phosphide NPs synthesized OLA/OA/ODE. (a) rhombohedral Sn₄P₃ NCs produced at 180 °C for 3 min, (b) hexagonal SnP NCs at 250 °C for 5 seconds, and (c) trigonal Sn₃P₄ NPs produced at 100 °C for 3 min.

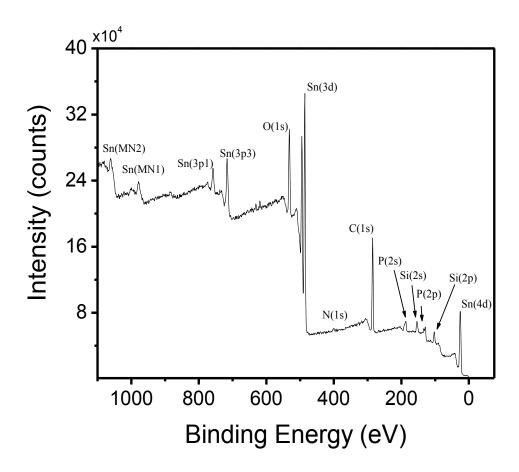


Figure S17. X-ray photoelectron spectrum (survey scan) of rhombohedral Sn₄P₃ NCs produced at 180 °C for 3 min.

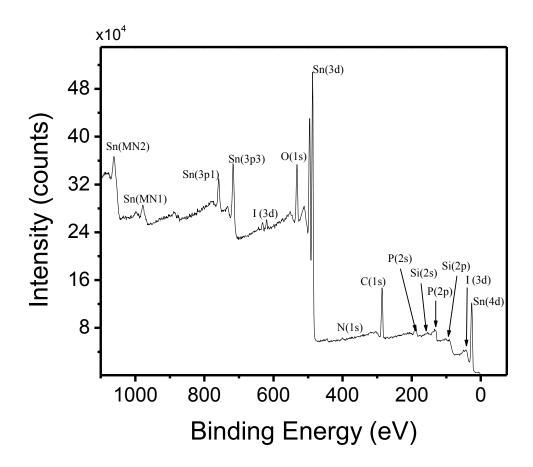


Figure S18. X-ray photoelectron spectrum (survey scan) of hexagonal SnP NCs produced at 250 °C for 5 seconds.

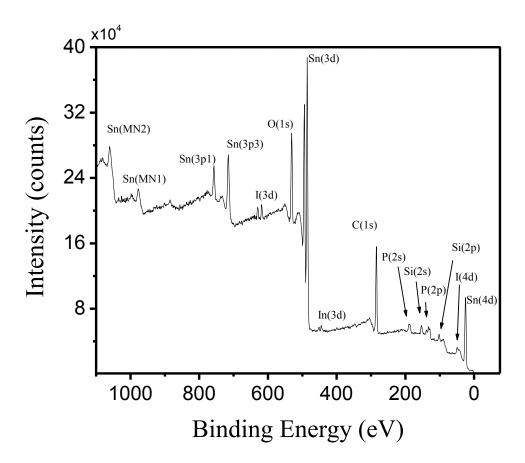


Figure S19. X-ray photoelectron spectrum (survey scan) of trigonal Sn₃P₄ NPs produced at 100 °C for 3 min.

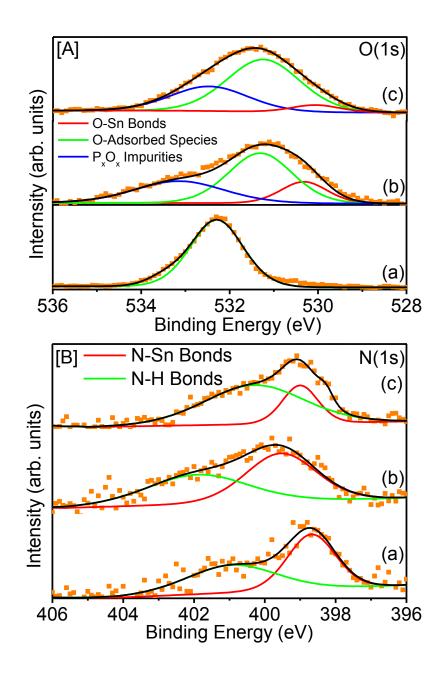


Figure S20. X-ray photoelectron spectra of (A) O(1s) and (B) N(1s) regions of (a) rhombohedral Sn₄P₃ NCs produced at 180 °C for 3 min., (b) hexagonal SnP NCs produced at 250 °C for 5 seconds, and (c) trigonal Sn₃P₄ NPs produced at 100 °C for 3 min.

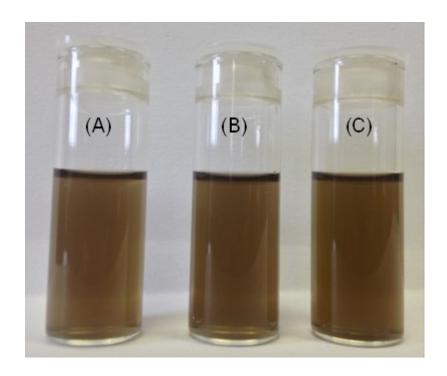


Figure S21. A photograph showing the colloidal stability of tin phosphide NPs in hexane. (A) trigonal Sn₃P₄ NPs synthesized at 100 °C, (B) rhombohedral Sn₄P₃ NCs synthesized at 180 °C, and (C) hexagonal SnP NCs synthesized at 250 °C.

References

(1) Ganesan, R.; Richter, K. W.; Schmetterer, C.; Effenberger, H.; Ipser, H. Synthesis of Single-Phase Sn₃P₄ by an Isopiestic Method. *Chem. Mater.* **2009**, *21*, 4108–4110.